## NSN 5961-01-009-4958

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-009-4958 **Inclosure Material:** Glass and metal **Overall Length:** 0.280 inches **Terminal Length:** 0.500 inches **Overall Height:** 0.280 inches **Overall Diameter:** 0.230 inches **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 collector to base voltage/static/emitter open **Current Rating Per Characteristic:** 50.00 milliamperes source cutoff current **Power Rating Per Characteristic:** 250.0 milliwatts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli

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